NSN 5961-01-316-5929

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-316-5929 **Inclosure Material:** Ceramic and metal **Overall Length:** Between 1.260 inches and 1.300 inches **Overall Diameter:** 3.950 inches **Mounting Method:** Compression **Features Provided:** Hermetically sealed case **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1200.0 repetitive peak reverse voltage and 1200.0 reverse voltage, instantaneous and 1440.0 nonrepetitive peak reverse voltage **Current Rating Per Characteristic:** 4170.00 amperes forward current, average of standard range and 2500.00 amperes forward current, average **Maximum Operating Tempurature Per Measurement Point:** 190.0 degrees celsius junction **Special Features:** Item must comply with requirements of defense electronics supply center production standard no. L04202; for navy nuclear propulsion plant products only **Terminal Type And Quantity:** 2 case Shelf Life: N/a **Unit Of Measure: Demilitarization:** No